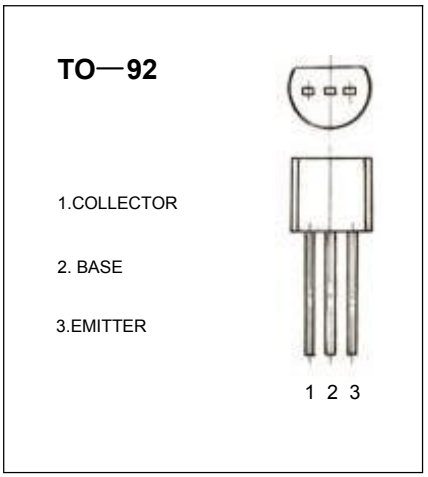
TO-92 Plastic-Encapsulate Transistors

BC337 TRANSISTOR（ NPN ）



FEATURES

Power dissipation

P_{CM}: 0.625 W（Tamb=25℃）

Collector current

I_{CM}: 0.8 A

Collector-base voltage

$V_{(BR)CBO}$: 50 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C=100μA, I_E=0	50			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C=10mA, I_B=0	45			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E=10μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=-45 V, I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=-40 V, I_B=0			0.2	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -4 V, I_C=0			0.1	μA
DC current gain(note)	H_{FE}（1）	V_{CE}=1V, I_C=100mA	100		630	
DC current gain(note)	H_{FE}（2）	V_{CE}=1V, I_C=300mA	60			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=500mA, I_B=50mA			-0.7	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=500mA, I_B=50mA			-1.2	V
Transition frequency	f_T	V_{CE}=5V, I_C=10mA f=100MHz	210			MHz

CLASSIFICATION OF HFE

Rank	1	2	3
Range	100-250	160-400	250-630